



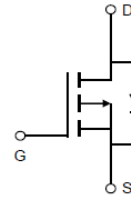
Product Summary

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

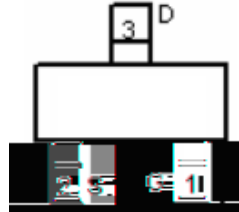


Trench technology

$R_{DS(ON)}$ to minimize conductive loss



Load Switches
DC/DC



| | |
|---------------------------|-----------|
| Part NO. | ZM350P02T |
| Marking | 350P02 |
| Packing Information | REEL TAPE |
| Basic ordering unit (pcs) | 3000 |

$T_c = 25$

| Parameter | Symbol | Rating | Unit |
|-------------------------------------|----------------|------------|------|
| Drain-Source Voltage | V_{DS} | -20 | V |
| Gate-Source Voltage | V_{GS} | ± 8 | V |
| Continuous Drain Current | $I_{D@TC=25}$ | -5.1 | A |
| | $I_{D@TC=75}$ | -3.8 | A |
| | $I_{D@TC=100}$ | -3.2 | A |
| Pulsed Drain Current | I_{DM} | -15 | A |
| Total Power Dissipation | P_D | 1.5 | W |
| Total Power Dissipation($T_A=25$) | $P_D@T_A=25$ | 0.7 | W |
| Operating Junction Temperature | T_J | -55 to 150 | |
| Storage Temperature | T_{STG} | -55 to 150 | |
| Single Pulse Avalanche Energy | E_{AS} | 25 | mJ |

Fig.1 Gate-Charge Characteristics

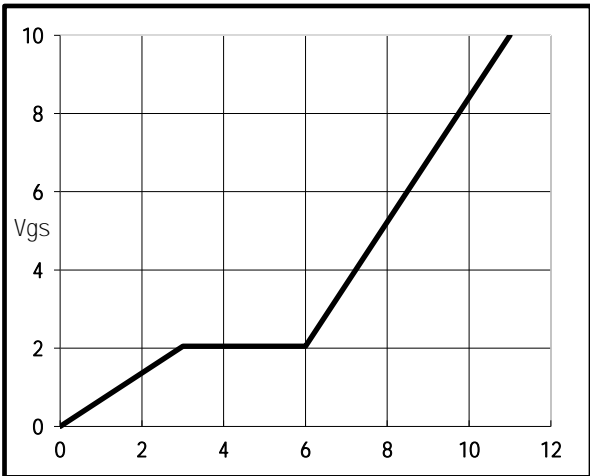


Fig.2 Capacitance Characteristics

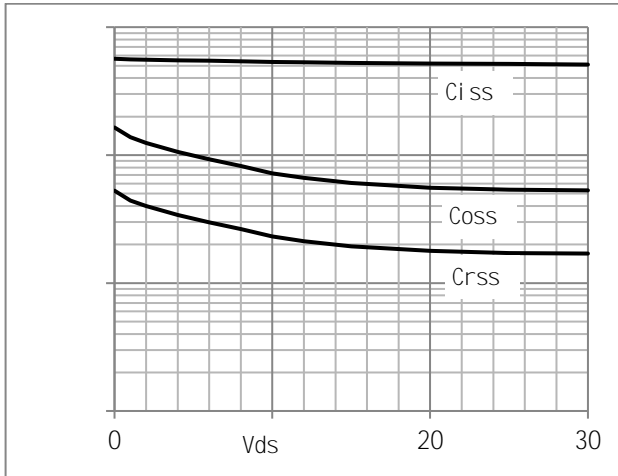


Fig.3 Power Dissipation Derating Curve

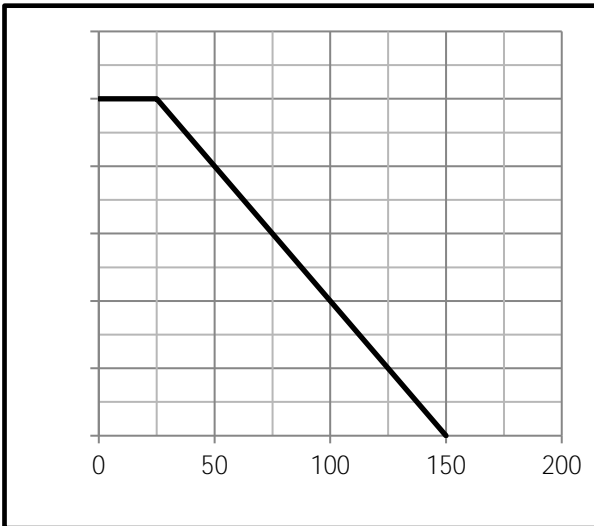


Fig.4 Typical output Characteristics

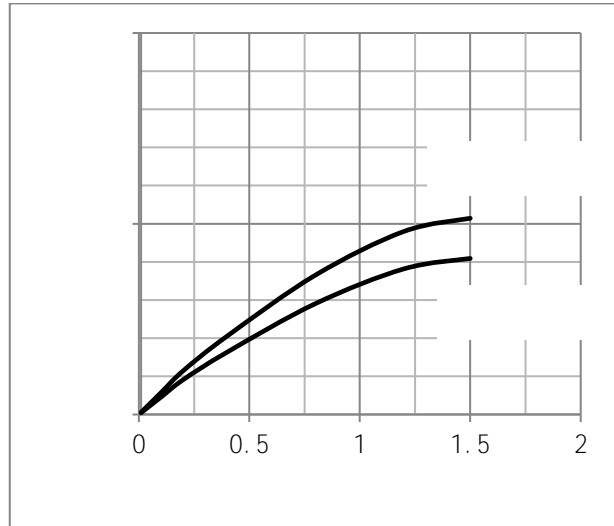


Fig.5 Threshold Voltage V.S Junction Temperature

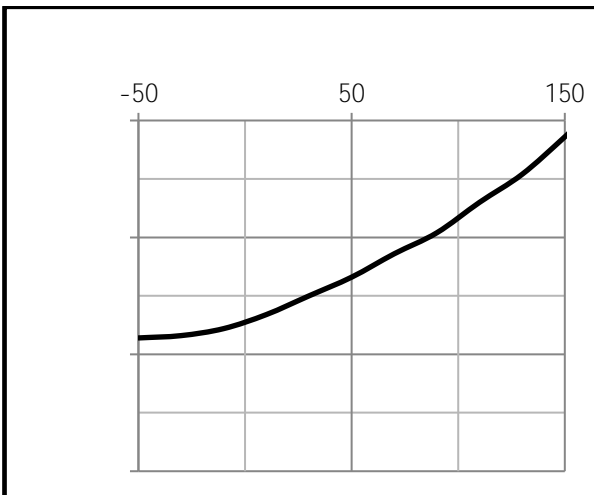
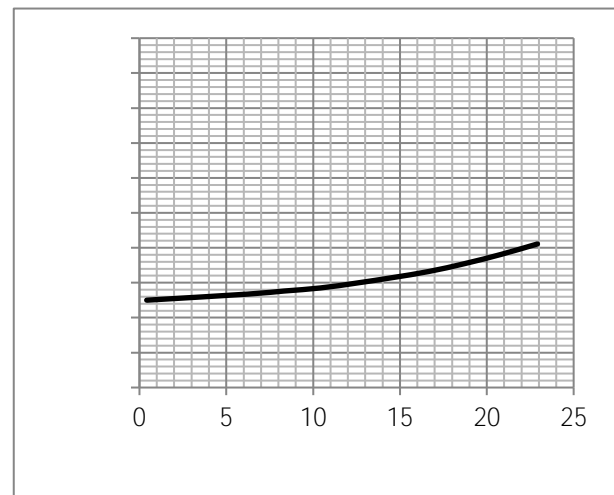


Fig.6 Resistance V.S Drain Current



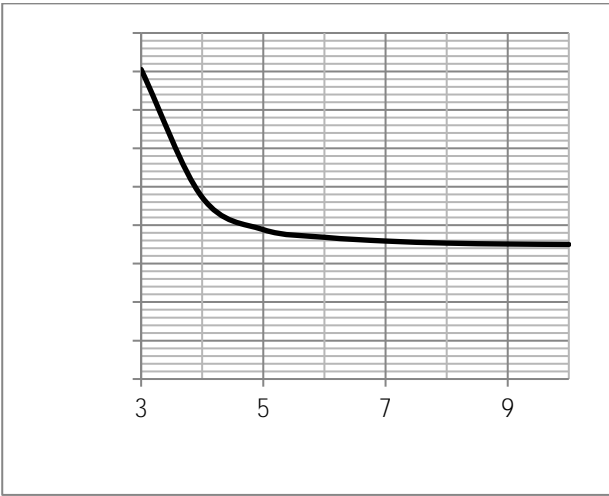


Fig.9 Switching Time Measurement Circuit

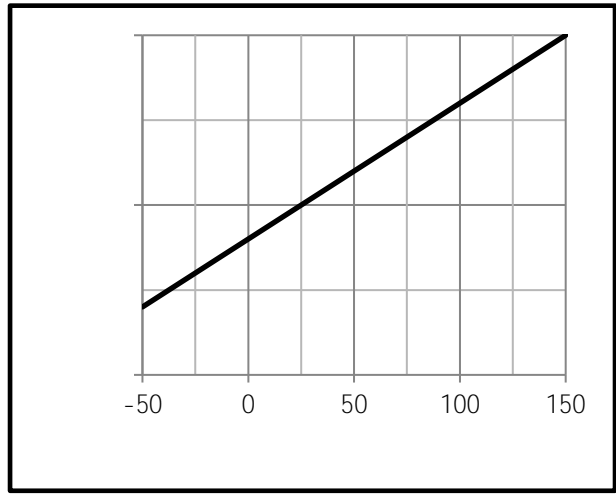


Fig.10 Gate Charge Waveform

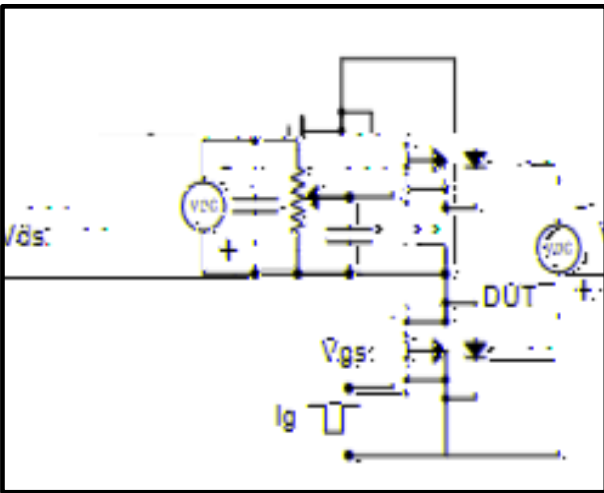


Fig.11 Switching Time Measurement Circuit

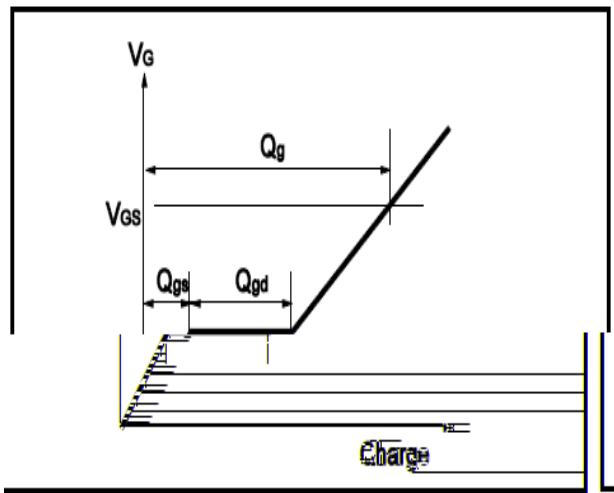


Fig.12 Gate Charge Waveform

